NSN 5962-01-113-9035

Memory Microcircuit - Page 1 of 1



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Body Length:

1.250 inches

Body Width:

0.500 inches

Body Height:

0.180 inches

Operating Tempurature Range:

+0.0/+70.0 degrees celsius

Storage Tempurature Range:

-65.0/+125.0 degrees celsius

Features Provided:

Hermetically sealed and programmable and monolithic and w/enable

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

14 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

6.0 volts power source

Time Rating Per Chacteristic:

450.00 nanoseconds propagation delay time, low to high level output and 450.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Test Data Document:

60854-312853 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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